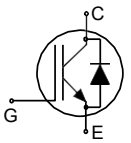
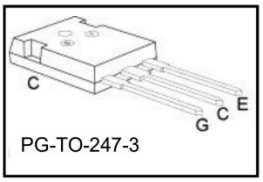
低损耗 DuoPack：采用第二代 **TrenchStop**® 技术的IGBT
搭配软、快速恢复反并联发射器控制二极管

- 短路耐受时间–10µs
- 设计用于：
  - 变频器
  - 不间断电源
- 适用于 1200 V 应用的第二代 **TrenchStop**® 具有以下特点：
  - 参数分布紧密
  - 高稳健性、温度稳定性
- 由于 $V_{CE(sat)}$ 具有正温度系数，因此易于并联
- 低电磁干扰
- 低栅极电荷
- 非常软、快速恢复的反并联发射级控制 HE 二极管
- 符合 JEDEC[1] 目标应用要求
- 无铅引脚镀层；符合 RoHS 标准
- 完整的产品品类和 PSpice 模型： http://www.infineon.cn/igbt/





Type	V_{CE}	I_C	$V_{CE(sat),Tj=25°C}$	$T_{j,max}$	Marking Code	Package
IKW15N120T2	1200V	15A	1.75V	175°C	K15T1202	PG-TO-247-3

最大额定值

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
DC collector current (Tj = 150°C)	I_C		A
T_C = 25°C		30	
T_C = 110°C		15	
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	60	
Turn off safe operating area	-	60	
$V_{CE} \leq$ 1200V, $T_j \leq$ 175°C			
Diode forward current (Tj = 150°C)	I_F		
T_C = 25°C		25	
T_C = 110°C		15	
Diode pulsed current, t_p limited by T_{jmax}	I_{Fpuls}	60	
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time[2)]	t_{SC}	10	µs
V_{GE} = 15V, $V_{CC} \leq$ 600V, $T_{j,start} \leq$ 175°C			
Power dissipation	P_{tot}	235	W
T_C = 25°C			
Operating junction temperature	T_j	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	
Wavesoldering only, temperature on leads only			

[1] J-STD-020 and JESD-022

[2)] 允许短路次数低于1000次；允许短路间隔时间大于1s

本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。为确认准确性，请务必访问 infineon.com 参考最新的英文版本（控制文档）。

热阻

Parameter	Symbol	Conditions	Max. Value	Unit
特性				
IGBT thermal resistance, junction – case	R_{thJC}		0.63	K/W
Diode thermal resistance, junction – case	R_{thJCD}		1.12	
Thermal resistance, junction – ambient	R_{thJA}		40	

电气特性，测于T_j=25 °C 的条件下，除非另有规定

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
静态特性						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}= 0 V, I_C= 500 µ A	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE}= 15 V, I_C= 15 A				
		T_j= 25 °C	-	1.7	2.2	
		T_j=150 °C	-	2.1	-	
		T_j=175 °C	-	2.2	-	
Diode forward voltage	V_F	V_{GE}= 0 V, I_F= 15 A				
		T_j= 25 °C	-	1.75	2.2	
		T_j=150 °C	-	1.8	-	
		T_j=175 °C	-	1.75	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C= 0 . 6 m A, V_{CE}= V_{GE}	5.2	5.8	6.4	
Zero gate voltage collector current	I_{CES}	V_{CE}= 1200 V, V_{GE}= 0 V				mA
		T_j= 25 °C	-	-	0.4	
		T_j= 150 °C	-	-	4.0	
		T_j=175 °C	-	-	20	
Gate-emitter leakage current	I_{GES}	V_{CE}= 0 V, V_{GE}= 20 V	-	-	600	nA
Transconductance	g_{fs}	V_{CE}= 20 V, I_C= 15 A	-	8	-	S

动态特性

Input capacitance	C_{iss}	V_{CE}= 25 V,	-	1000	-	pF
Output capacitance	C_{oss}	V_{GE}= 0 V,	-	100	-	
Reverse transfer capacitance	C_{rss}	f= 1 MHz	-	56	-	
Gate charge	Q_{Gate}	V_{CC}= 960 V, I_C= 15 A V_{GE}= 15 V	-	93	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13	-	nH
Short circuit collector current[1)]	$I_{C(SC)}$	V_{GE}= 15 V, $t_{SC}\leq$ 10 µs V_{CC}= 600 V, $T_{j,start}$= 25 °C $T_{j,start}$= 175 °C	-	 82 60	-	A

开关特性，感性负载，测于T_j= 25 °C的条件下

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT特性						
Turn-on delay time	$t_{d(on)}$	T_j= 25 °C, V_{CC}= 600 V, I_C= 15 A, V_{GE}= 0 / 15 V, R_G= 41 . 8 Ω, L_{σ}[2)]=126 n H, C_{σ}[2)]= 34 pF Energy losses include “tail” and diode reverse recovery.	-	32	-	ns
Rise time	t_r		-	25	-	
Turn-off delay time	$t_{d(off)}$		-	362	-	
Fall time	t_f		-	95	-	
Turn-on energy	E_{on}		-	1.25	-	mJ
Turn-off energy	E_{off}		-	0.8	-	
Total switching energy	E_{ts}		-	2.05	-	
反并联二极管特性						
Diode reverse recovery time	t_{rr}	T_j= 25 °C, V_R= 600 V, I_F= 15 A, di_F/dt= 450 A/ µs	-	300	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.3		µC
Diode peak reverse recovery current	I_{rrm}		-	10		A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	215	-	A/µs

[1)] 允许短路次数低于1000次；允许短路间隔时间大于1s

[2)]图E中动态测试电路产生的漏感L_{σ}和杂散电容C_{σ}。

开关特性，感性负载， T_j = 175 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT特性						
Turn-on delay time	$t_{d(on)}$	T_j=175 °C V_{CC}= 600 V, I_C= 15 A, V_{GE}= 0 / 15 V, R_G= 41 . 8 Ω , L_σ[1)] = 315 n H, C_σ[1)] =34 pF Energy losses include “tail” and diode reverse recovery.	-	31	-	ns
Rise time	t_r		-	30	-	
Turn-off delay time	$t_{d(off)}$		-	450	-	
Fall time	t_f		-	176	-	
Turn-on energy	E_{on}		-	1.5	-	mJ
Turn-off energy	E_{off}		-	1.3	-	
Total switching energy	E_{ts}		-	2.8	-	
反并联二极管特性						
Diode reverse recovery time	t_{rr}	T_j=175 °C V_R= 600 V, I_F= 15 A, di_F/dt = 460 A/ µs	-	460	-	ns
Diode reverse recovery charge	Q_{rr}		-	2.65	-	µC
Diode peak reverse recovery current	I_{rrm}		-	13	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	123		A/µs

[1)]图E中动态测试电路产生的漏感L_σ和杂散电容C_σ。

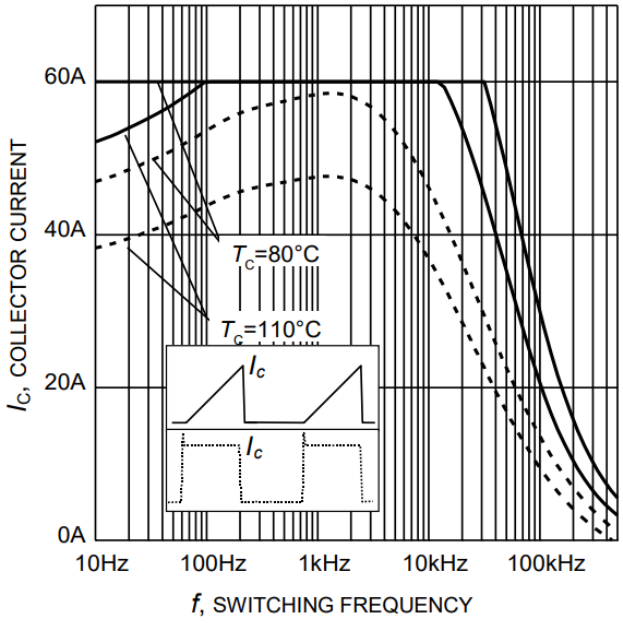


Figure 1. Collector current as a function of switching frequency
($T_j \le 175°C$, $D = 0.5$, $V_{CE} = 600V$, $V_{GE} = 0/+15V$, $R_G = 41.8\Omega$)

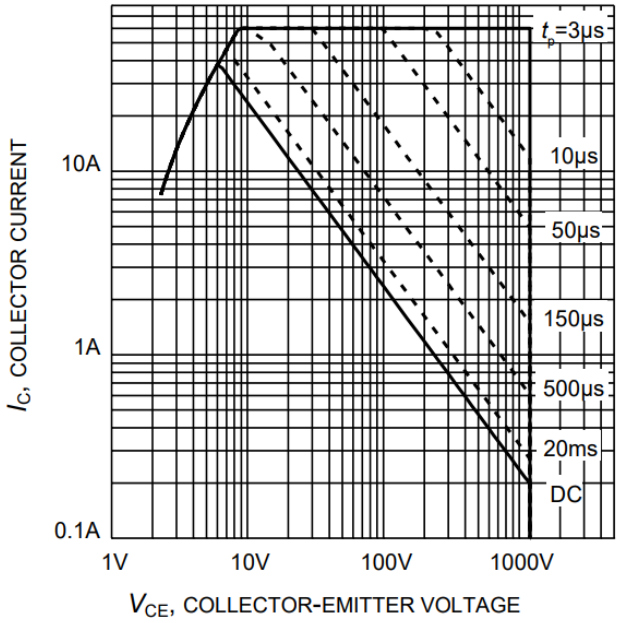


Figure 2. Safe operating area
($D = 0$, $T_C = 25°C$, $T_j \le 175°C$; V_{GE}=15V)

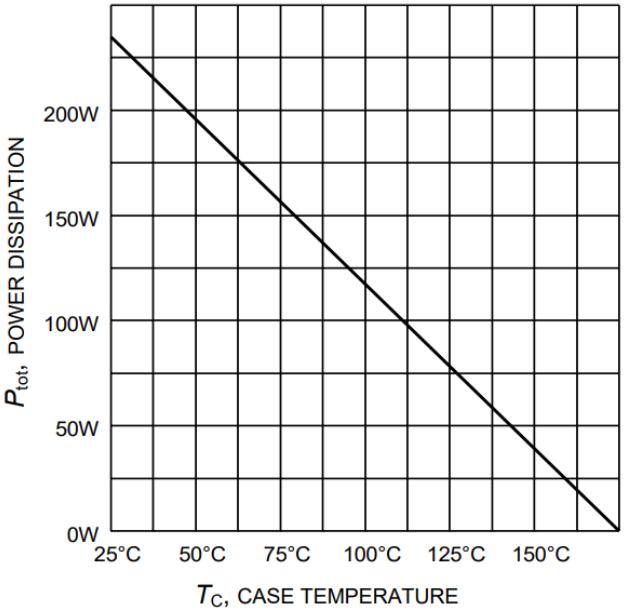


Figure 3. Maximum power dissipation as a function of case temperature
($T_j \le 175°C$)

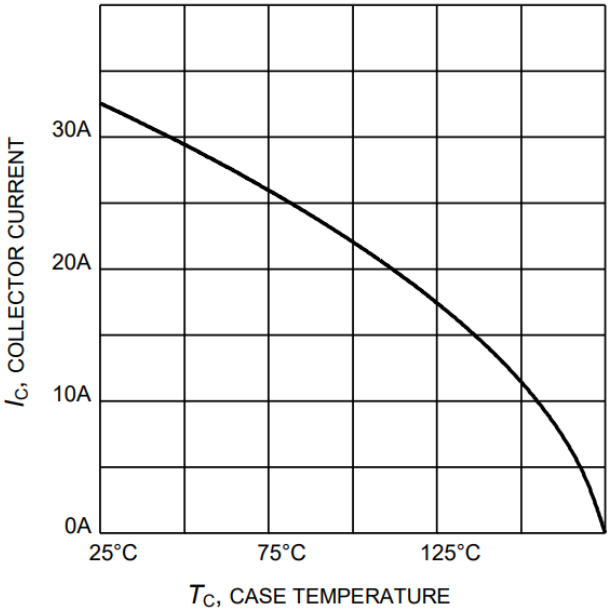


Figure 4. Maximum DC Collector current as a function of case temperature
($V_{GE} \ge 15V$, $T_j \le 175°C$)

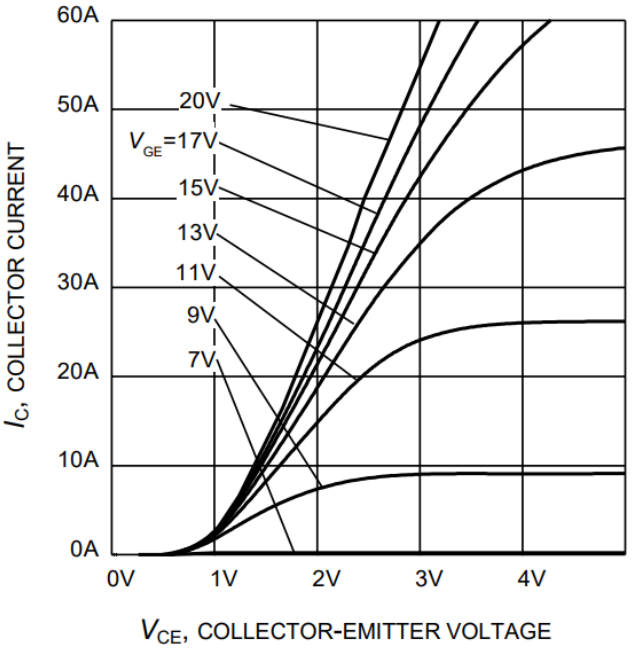


Figure 5. Typical output characteristic
(T_j = 25°C)

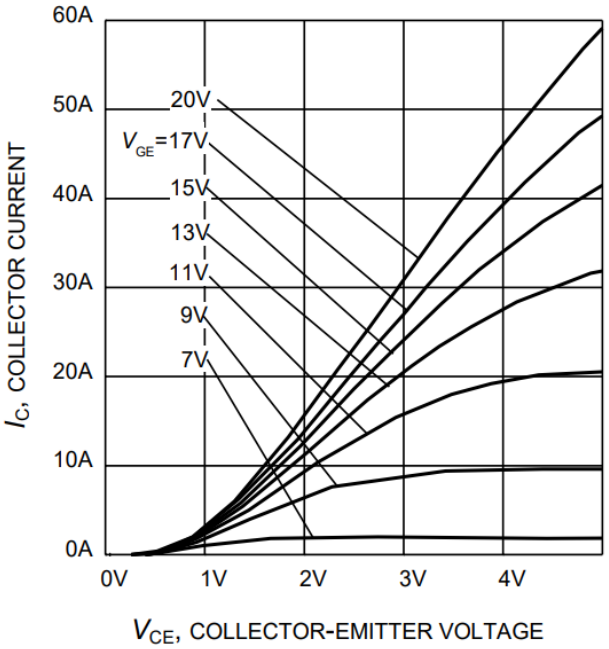


Figure 6. Typical output characteristic
(T_j = 175°C)

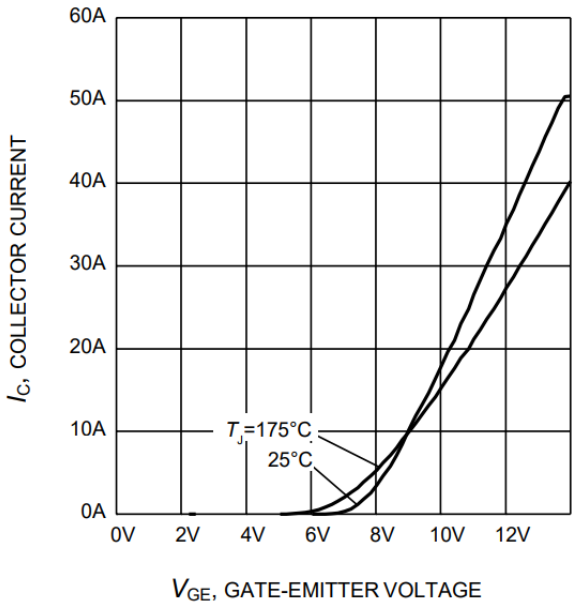


Figure 7. Typical transfer characteristic
(V_{CE}=20V)

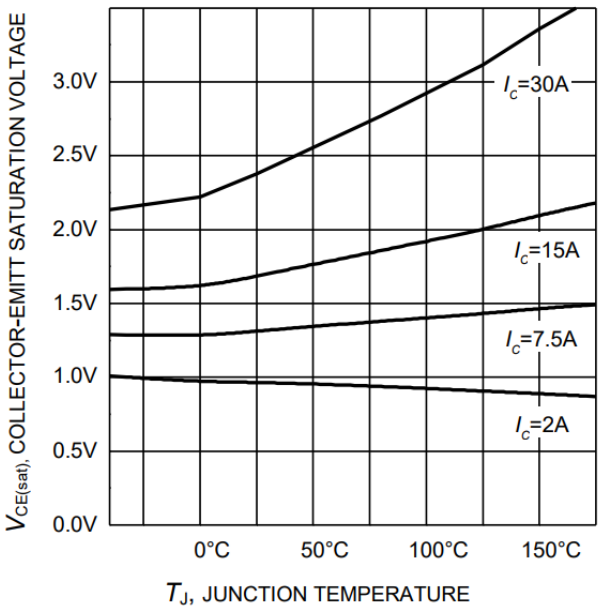


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE} = 15V)

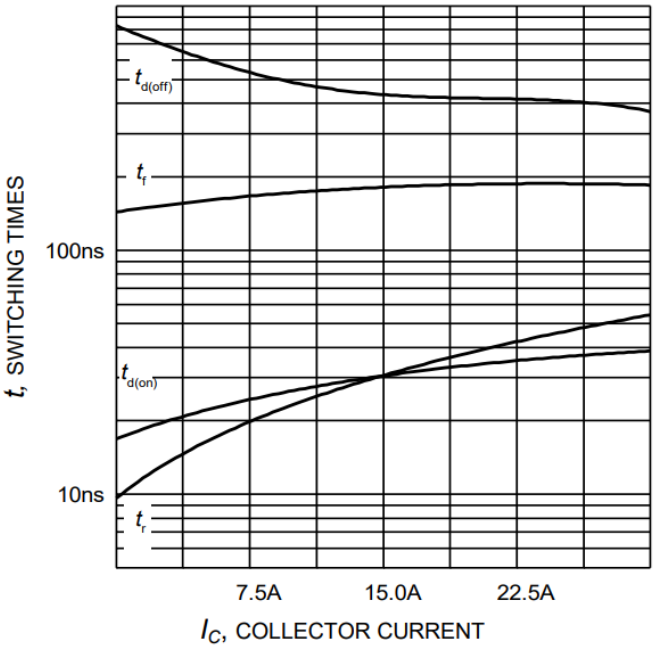


Figure 9. Typical switching times as a function of collector current
(inductive load, T_J=175°C, V_{CE}=600V, V_{GE}=0/15V, R_G=41.8Ω, Dynamic test circuit in Figure E)

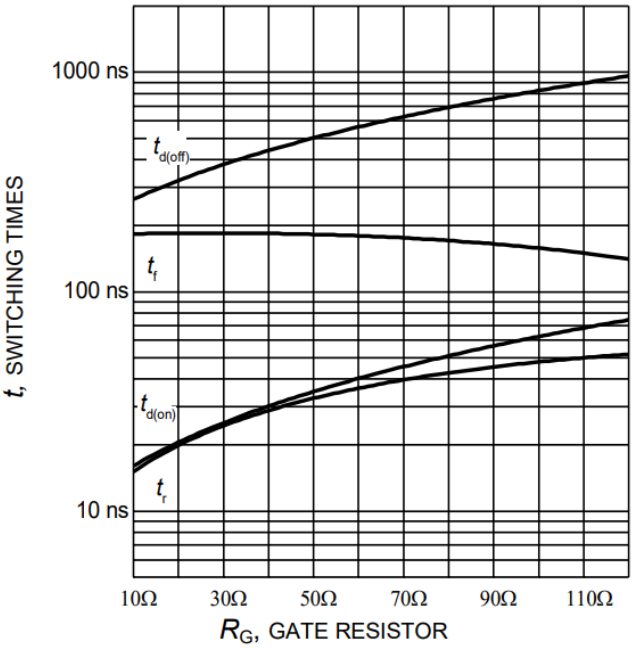


Figure 10. Typical switching times as a function of gate resistor
(inductive load, T_J=175°C, V_{CE}=600V, V_{GE}=0/15V, I_C=15A, Dynamic test circuit in Figure E)

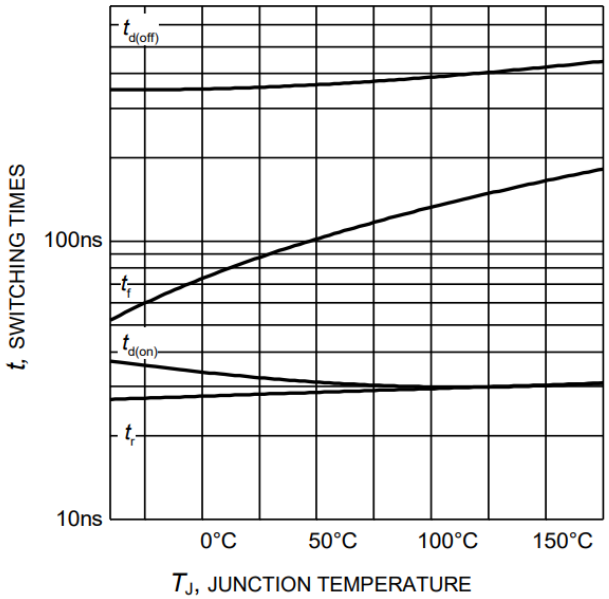


Figure 11. Typical switching times as a function of junction temperature
(inductive load, V_{CE}=600V, V_{GE}=0/15V, I_C=15A, R_G=41.8Ω, Dynamic test circuit in Figure E)

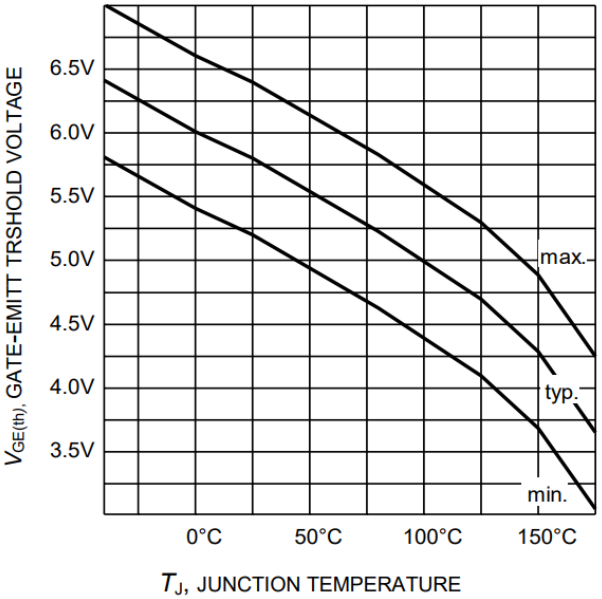


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
(I_C = 600µA)

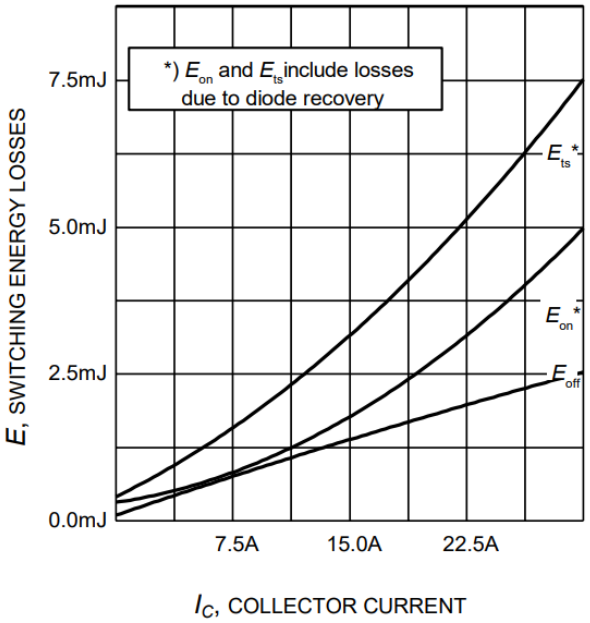


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, T_J=175°C, V_{CE}=600V, V_{GE}=0/15V, R_G=41.8Ω, Dynamic test circuit in Figure E)

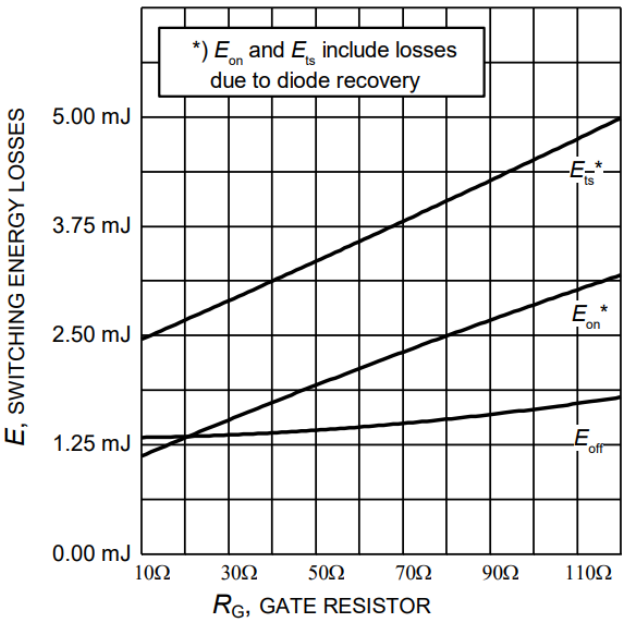


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, T_J=175°C, V_{CE}=600V, V_{GE}=0/15V, I_C=15A, Dynamic test circuit in Figure E)

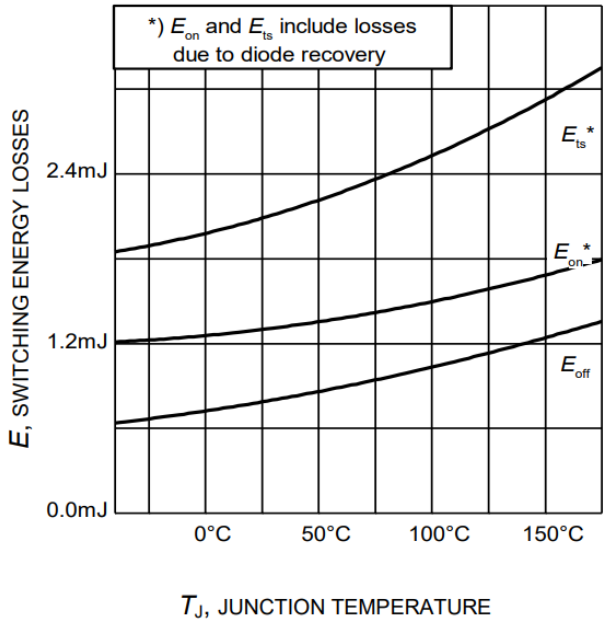


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, V_{CE}=600V, V_{GE}=0/15V, I_C=15A, R_G=41.8Ω, Dynamic test circuit in Figure E)

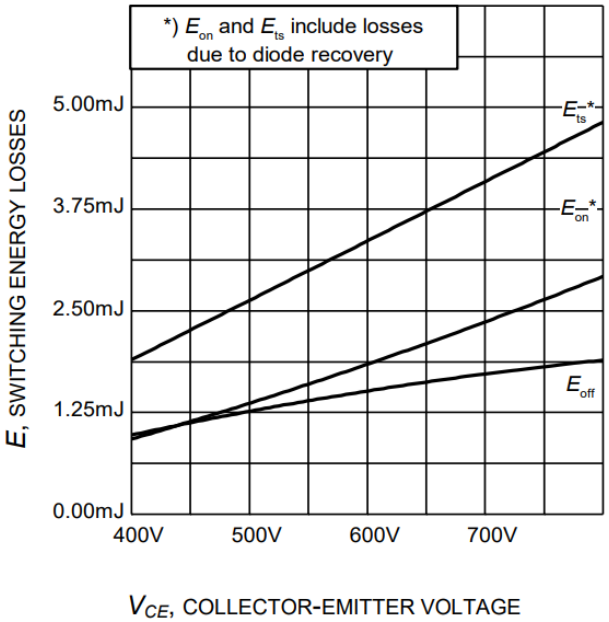


Figure 16. Typical switching energy losses as a function of collector emitter voltage
(inductive load, T_J=175°C, V_{GE}=0/15V, I_C=15A, R_G=41.8Ω, Dynamic test circuit in Figure E)

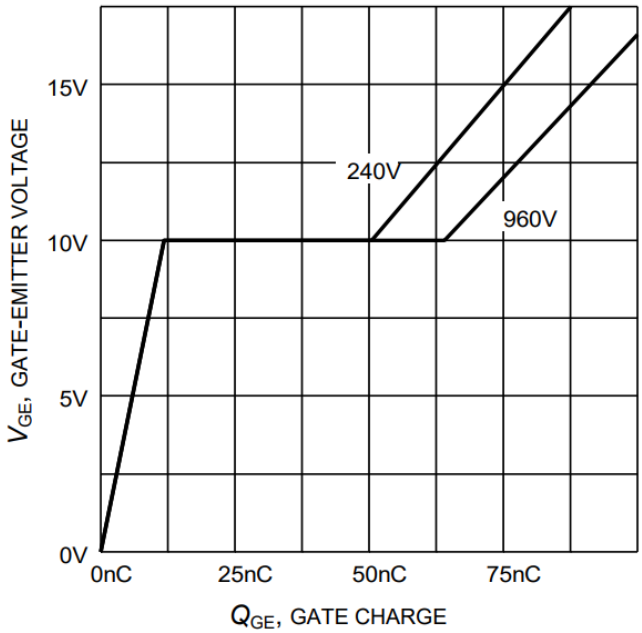


Figure 17. Typical gate charge
(I_C=15 A)

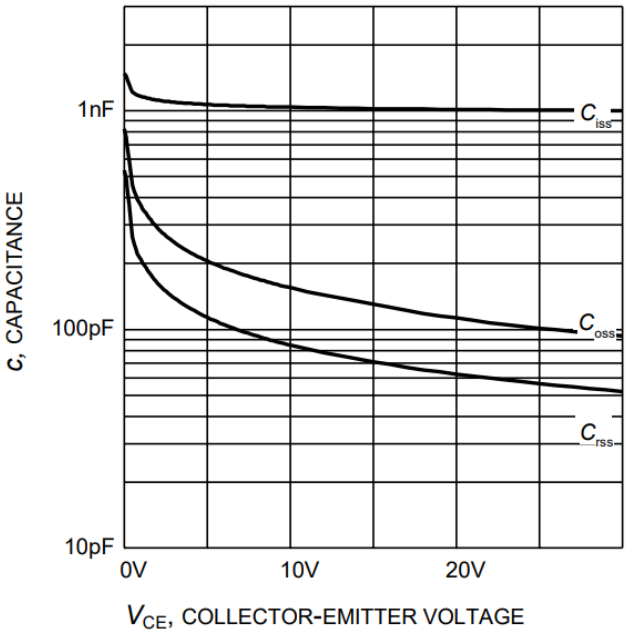


Figure 18. Typical capacitance as a function of collector-emitter voltage
(V_{GE}=0V, f = 1 MHz)

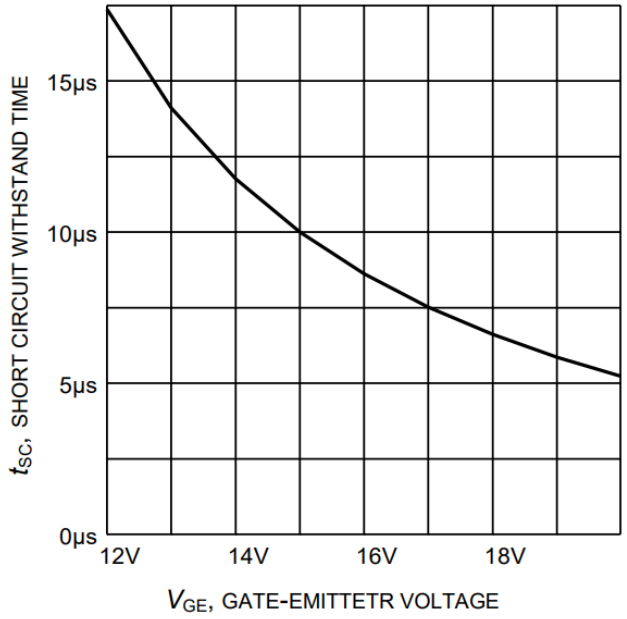


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE}=600V, start at T_J≤175°C)

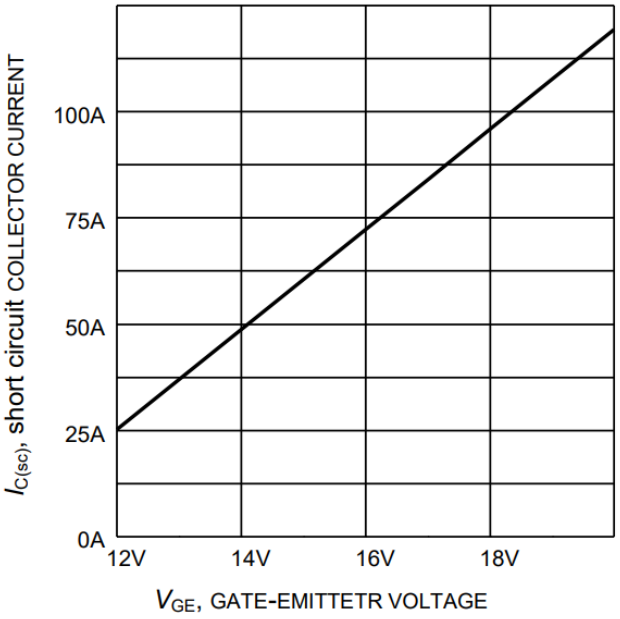


Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
(V_{CE} ≤ 600V, $T_{j,start}$ =175°C)

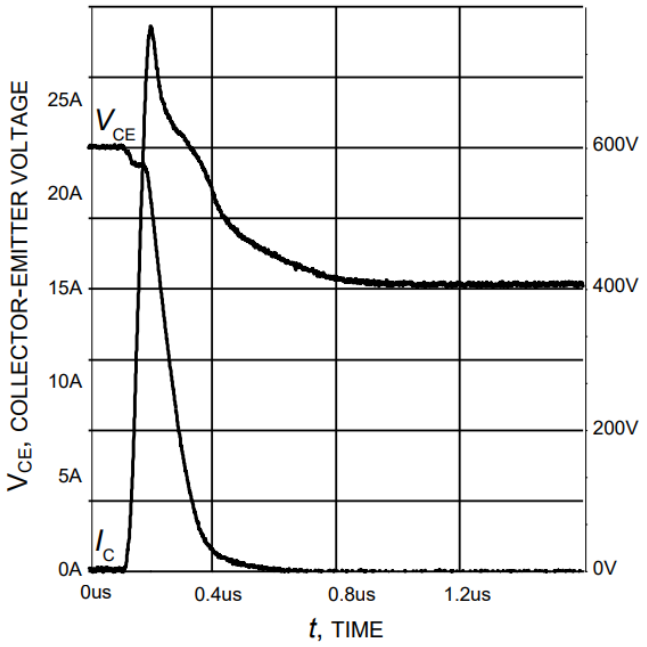


Figure 21. Typical turn on behavior
(V_{GE}=0/15V, R_G=41.8Ω, T_j = 175°C,
Dynamic test circuit in Figure E)

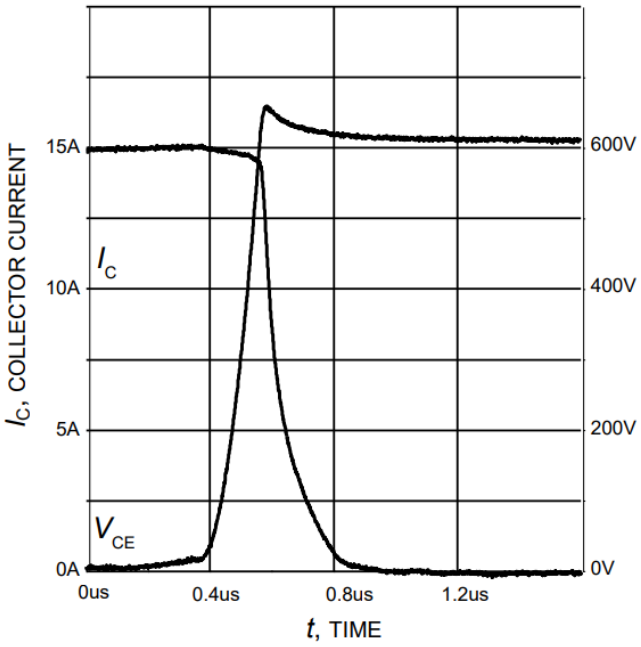


Figure 22. Typical turn off behavior
(V_{GE}=15/0V, R_G=41.8Ω, T_j = 175°C,
Dynamic test circuit in Figure E)

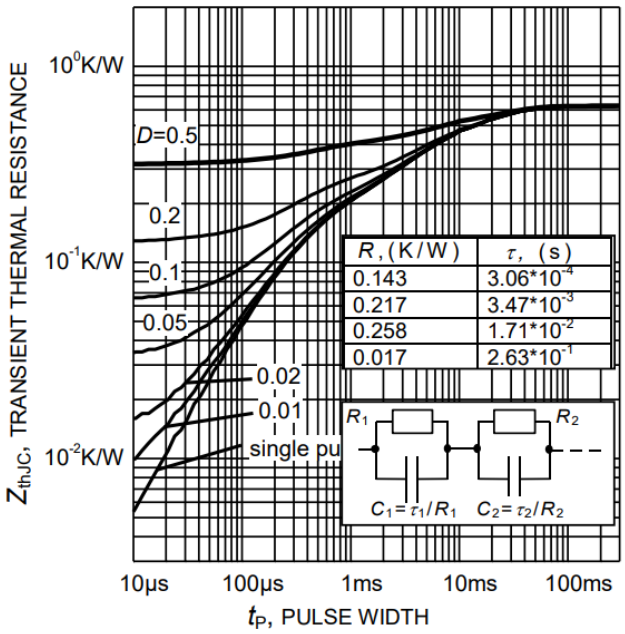


Figure 23. IGBT transient thermal resistance
($D = t_p / T$)

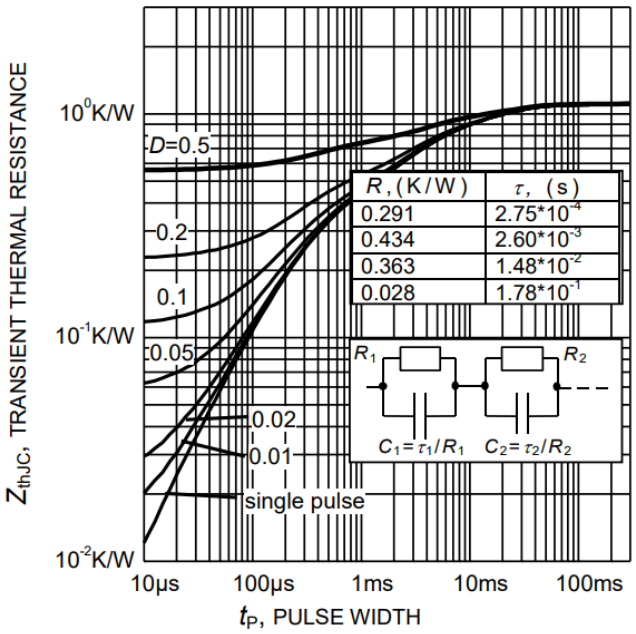


Figure 24. Diode transient thermal impedance as a function of pulse width
($D=t_P/T$)

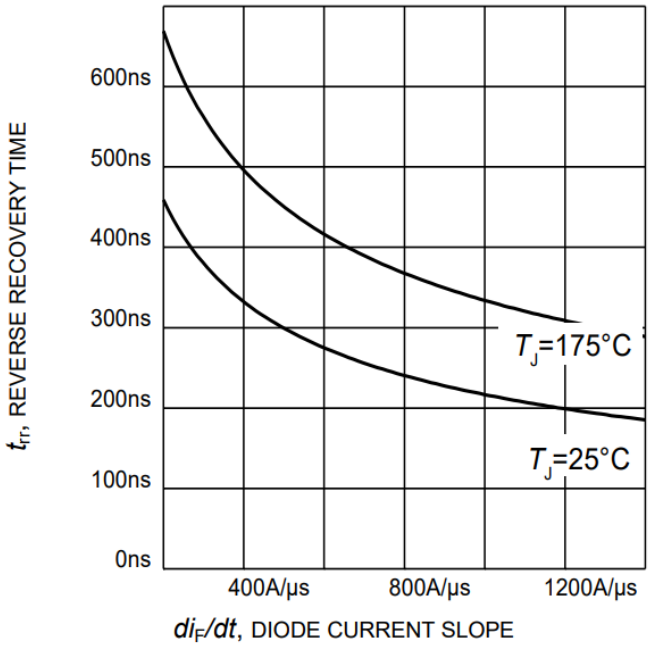


Figure 23. Typical reverse recovery time as a function of diode current slope
(V_R=600V, I_F=15A,
Dynamic test circuit in Figure E)

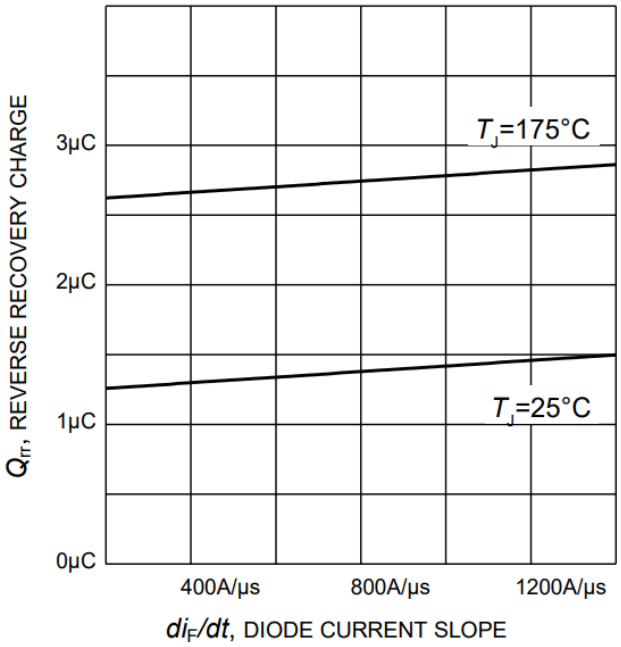


Figure 24. Typical reverse recovery charge as a function of diode current slope
(V_R=600V, I_F=15A,
Dynamic test circuit in Figure E)

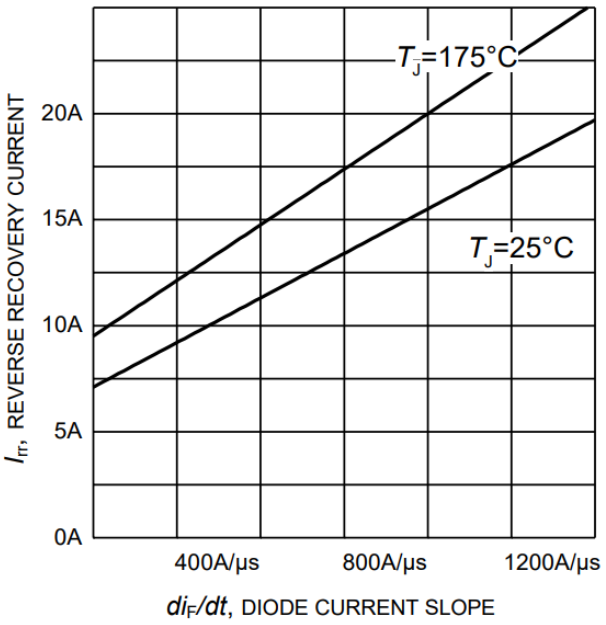


Figure 25. Typical reverse recovery current as a function of diode current slope
(V_R=600V, I_F=15A,
Dynamic test circuit in Figure E)

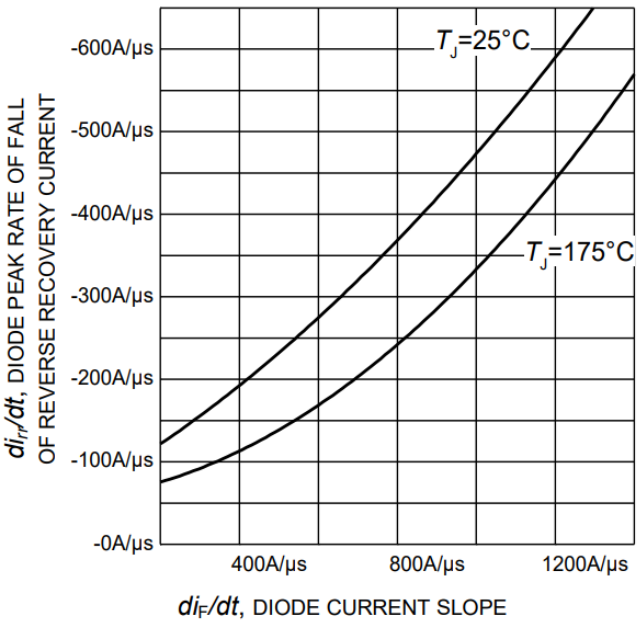


Figure 26. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope
(V_R=600V, I_F=15A,
Dynamic test circuit in Figure E)

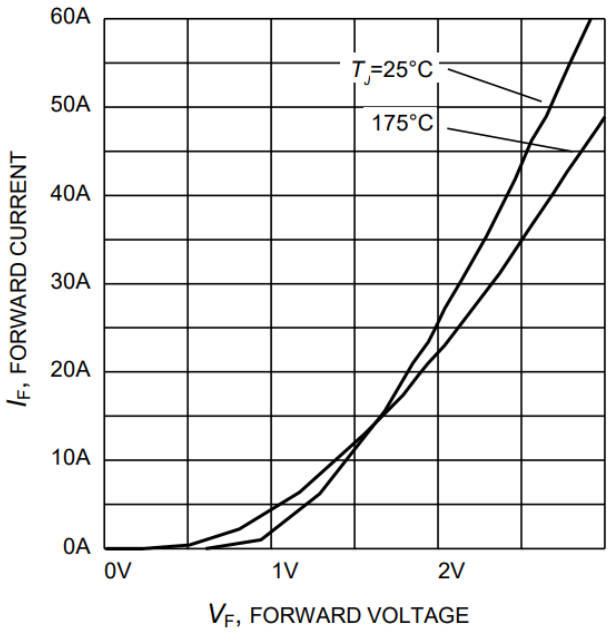


Figure 27. Typical diode forward current as a function of forward voltage

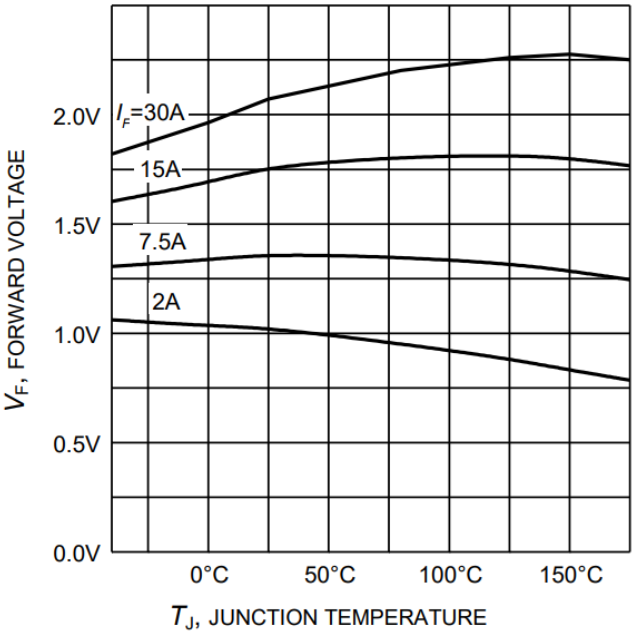
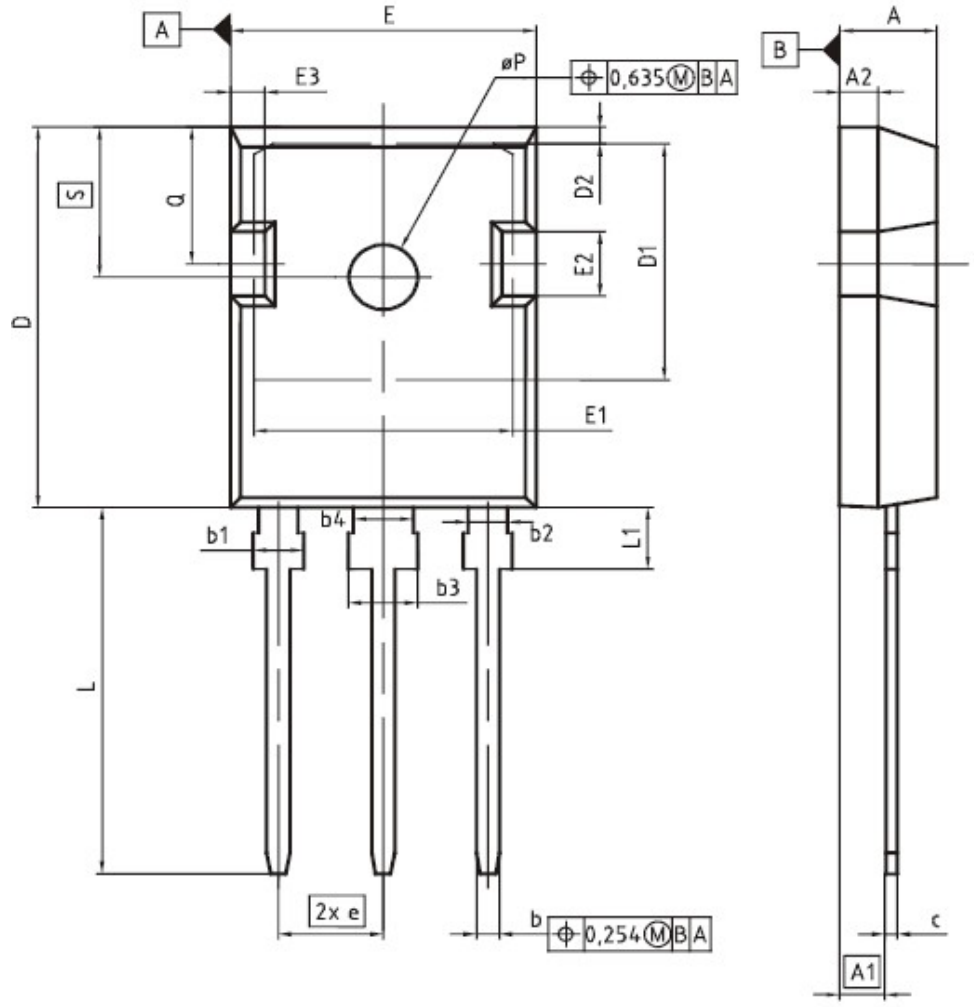


Figure 28. Typical diode forward voltage as a function of junction temperature

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4,83	5,21	0,190	0,205
A1	2,27	2,54	0,089	0,100
A2	1,85	2,16	0,073	0,085
b	1,07	1,33	0,042	0,052
b1	1,90	2,41	0,075	0,095
b2	1,90	2,16	0,075	0,085
b3	2,87	3,38	0,113	0,133
b4	2,87	3,13	0,113	0,123
c	0,55	0,68	0,022	0,027
D	20,80	21,10	0,819	0,831
D1	16,25	17,65	0,640	0,695
D2	0,95	1,35	0,037	0,053
E	15,70	16,13	0,618	0,635
E1	13,10	14,15	0,516	0,557
E2	3,68	5,10	0,145	0,201
E3	1,00	2,60	0,039	0,102
e	5,44 (BSC)		0,214 (BSC)	
N	3		3	
L	19,80	20,32	0,780	0,800
L1	4,10	4,47	0,161	0,176
øP	3,50	3,70	0,138	0,146
Q	5,49	6,00	0,216	0,236
S	6,04	6,30	0,238	0,248

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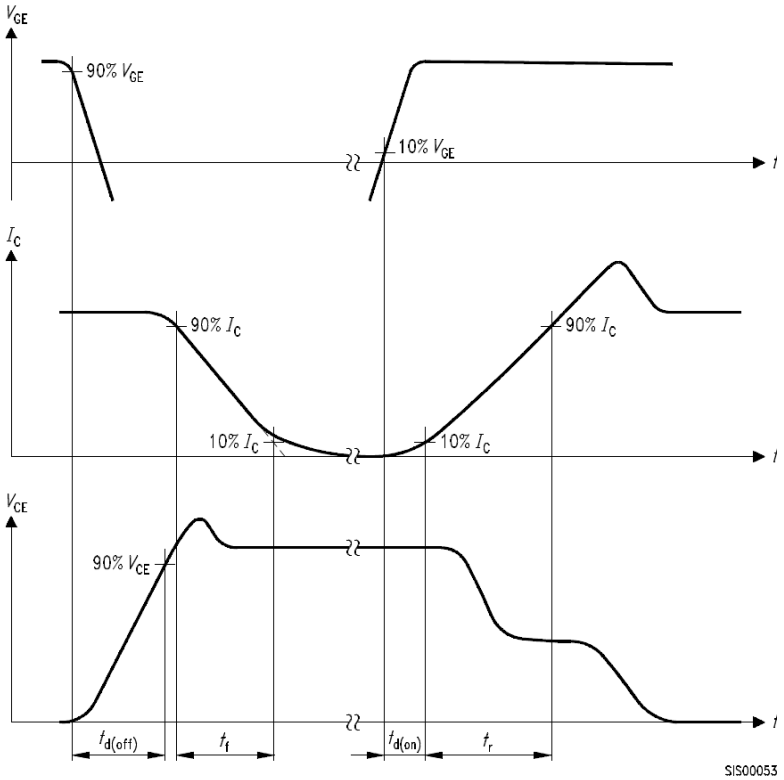


Figure A. Definition of switching times

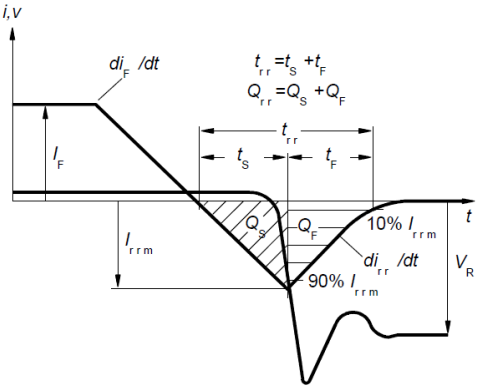


Figure C. Definition of diodes switching characteristics

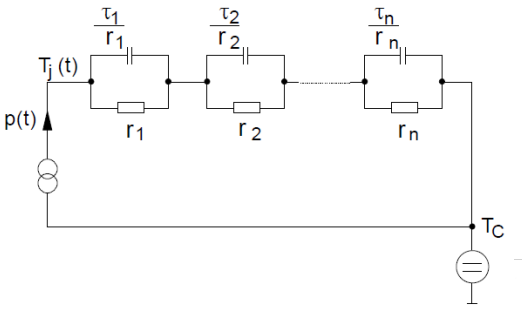


Figure D. Thermal equivalent circuit

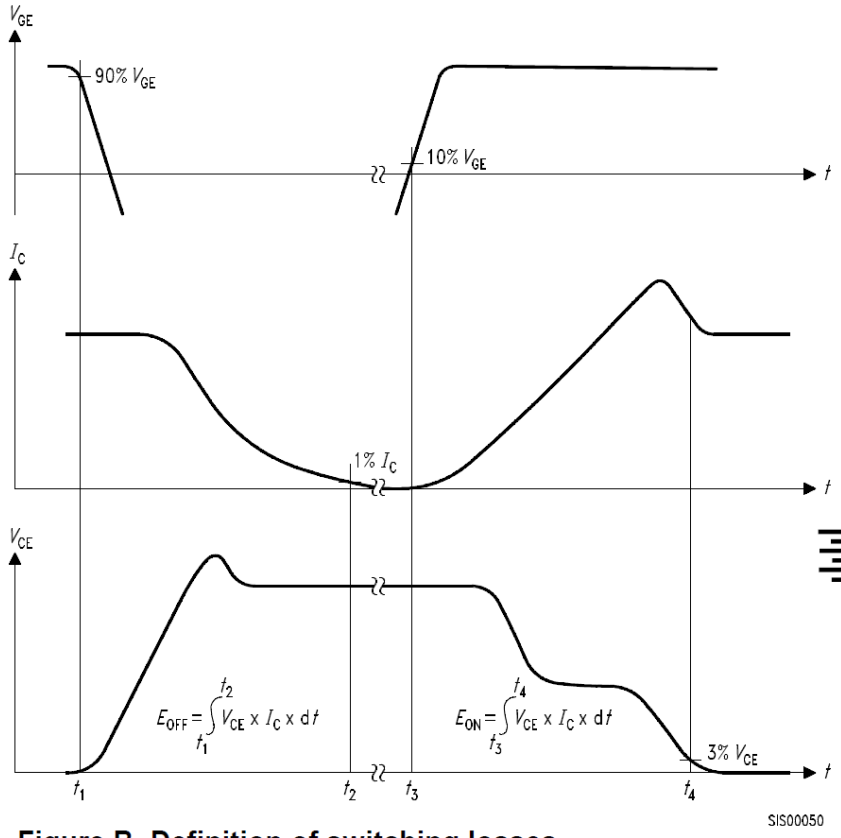


Figure B. Definition of switching losses

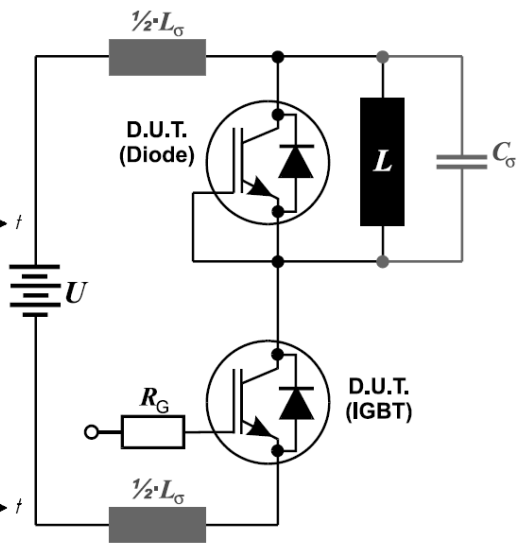


Figure E. Dynamic test circuit

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